

DESCRIPTION The 2SB1150 is a darlington transistor built-in a zener diode at B-C and a dumper diode at E-C.

It is suitable for use to operate from IC without predriver, such as hammer driver.

- FEATURES**
- High DC Current Gain.
 - Built-in a Zener Diode at B-C and a Dumper Diode at E-C.
 - Low Collector Saturation Voltage.
 - High Power Dissipation: $P_T = 1.3 \text{ W}$ (at $T_a = 25^\circ \text{C}$)

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature -55 to $+150^\circ \text{C}$
- Junction Temperature $+150^\circ \text{C}$ Maximum

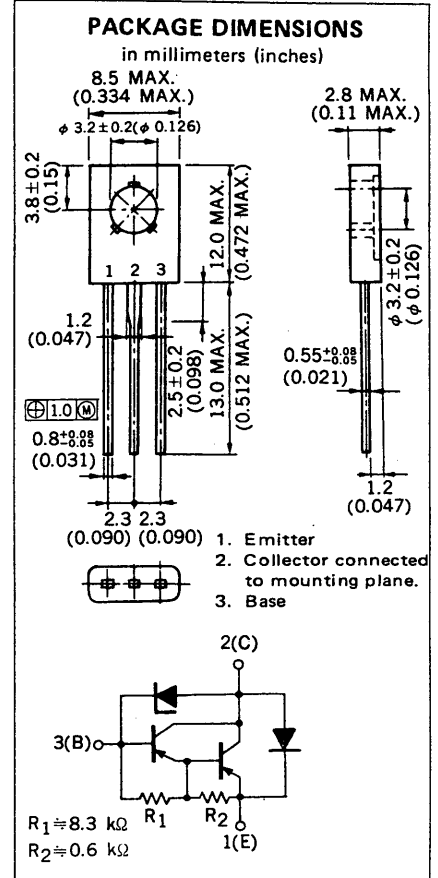
Maximum Power Dissipations

- Total Power Dissipation ($T_a = 25^\circ \text{C}$) 1.3 W
- Total Power Dissipation ($T_c = 25^\circ \text{C}$) 15 W

Maximum Voltages and Currents ($T_a = 25^\circ \text{C}$)

- V_{CBO} Collector to Base Voltage $-60 \pm 10 \text{ V}$
- V_{CEO} Collector to Emitter Voltage $-60 \pm 10 \text{ V}$
- V_{EBO} Emitter to Base Voltage -8.0 V
- $I_{C(DC)}$ Collector Current $\mp 3.0 \text{ A}$
- $I_{C(\text{pulse})}$ Collector Current $\mp 5.0 \text{ A}$

* $PW \leq 10 \text{ ms}$, Duty Cycle $\leq 50 \%$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ \text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE1}^{**}	DC Current Gain	2000		15000	—	$V_{CE} = -2.0 \text{ V}$, $I_C = -1.5 \text{ A}$
h_{FE2}^{**}	DC Current Gain	1000			—	$V_{CE} = -2.0 \text{ V}$, $I_C = -3.0 \text{ A}$
V_{CBO}	Collector to Base Voltage	-50	-60	-70	V	$I_C = -1.0 \text{ mA}$, $I_E = 0$
V_{CEO}	Collector to Emitter Voltage	-50	-60	-70	V	$I_C = -10 \text{ mA}$, $R_{BE} = \infty$
t_{on}	Turn On Time		0.5		μs	$I_C = 1.5 \text{ A}$, $R_L = 27 \Omega$ $I_{B1} = -I_{B2} = 1.5 \text{ mA}$, $V_{CC} \cong 40 \text{ V}$
t_{stg}	Storage Time		2.0		μs	
t_f	Fall Time		1.0		μs	
I_{CBO}	Collector Cutoff Current			-10	μA	$V_{CB} = -40 \text{ V}$, $I_E = 0$
I_{EBO}	Emitter Cutoff Current			-1.0	mA	$V_{EB} = -5.0 \text{ V}$, $I_C = 0$
$V_{CE(\text{sat})}^{**}$	Collector Saturation Voltage		-0.9	-1.2	V	$I_C = -1.5 \text{ A}$, $I_B = -1.5 \text{ mA}$
$V_{BE(\text{sat})}^{**}$	Base Saturation Voltage		-1.5	-2.0	V	$I_C = -1.5 \text{ A}$, $I_B = -1.5 \text{ mA}$

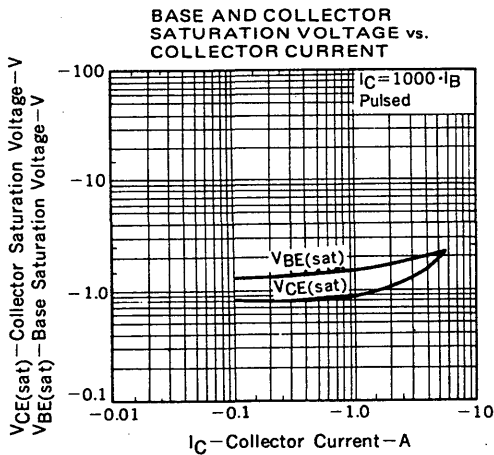
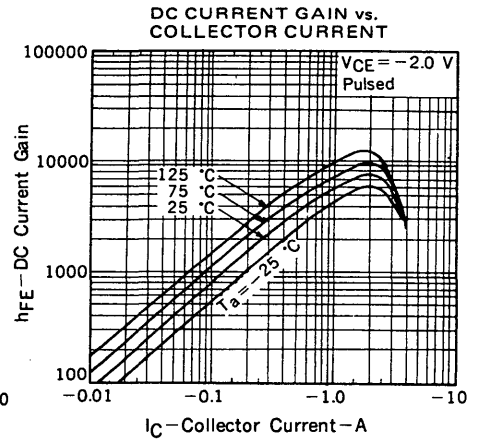
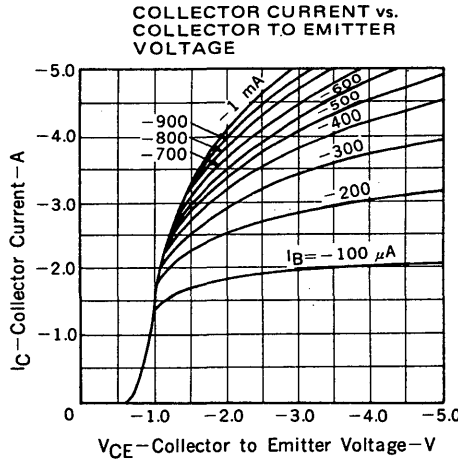
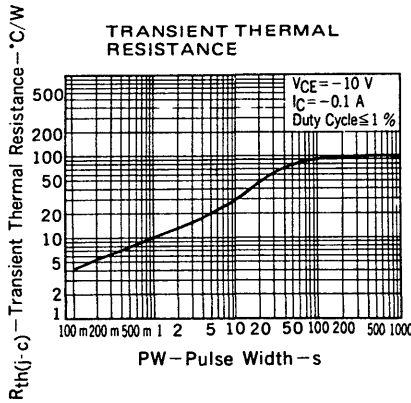
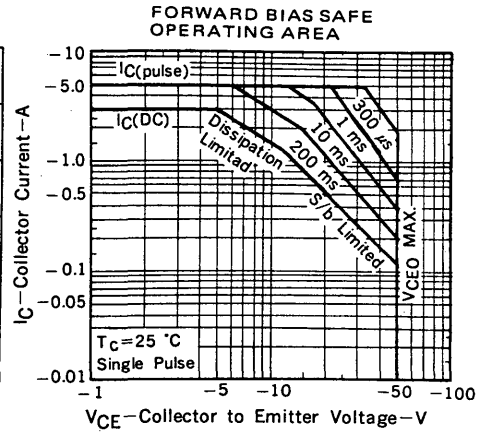
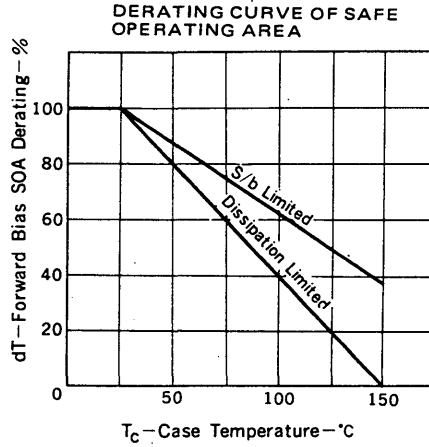
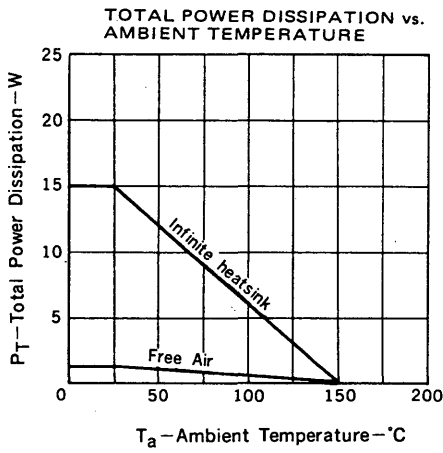
** Pulsed / $PW \leq 350 \mu\text{s}$, Duty Cycle $\leq 2 \%$

Classification of h_{FE1}

Rank	M	L	K
Range	2000 to 5000	3000 to 7000	5000 to 15000

Test Conditions: $V_{CE} = -2.0 \text{ V}$, $I_C = -1.5 \text{ A}$

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



SWITCHING TIME (t_{on} , t_{stg} , t_f) TEST CIRCUIT

